Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Texas Instruments
ISO7240ADW

For any questions, you can email us directly:
sales@integrated-circuit.com

Not Recommended for New Designs

1-Mbps QUAD DIGITAL ISOLATORS

Check for Samples: ISO7240A, ISO7241A, ISO7242A

FEATURES

- **4000-V_{peak} Isolation, 560-V_{peak} V_{IORM}**
  - **UL 1577 , IEC 60747-5-2 (VDE 0884, Rev 2), IEC 61010-1, IEC 60950-1 and CSA Approved**
- **4 kV ESD Protection**
- **Operate With 3.3-V or 5-V Supplies**
- **Typical 25-Year Life at Rated Working Voltage (See Application Note (SLLA197) and Figure 10)**
- **High Electromagnetic Immunity (See Application Report (SLLA181))**
- **–40°C to 125°C Operating Range**

APPLICATIONS

- **Industrial Fieldbus**
- **Computer Peripheral Interface**
- **Servo Control Interface**
- **Data Acquisition**

DESCRIPTION

See the Product Notification section. The ISO7240A, ISO7241A and ISO7242A are quad-channel digital isolators with multiple channel configurations and output enable functions. These devices have logic input and output buffers separated by TI's silicon dioxide (SiO_2) isolation barrier. Used in conjunction with isolated power supplies, these devices block high voltage, isolate grounds, and prevent noise currents from entering the local ground and interfering with or damaging sensitive circuitry.

The ISO7240A has all four channels in the same direction while the ISO7241A has three channels the same direction and one channel in opposition. The ISO7242A has two channels in each direction.

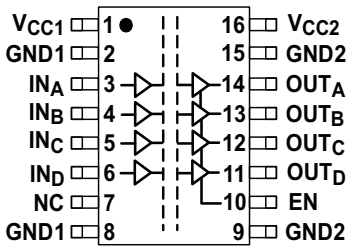
The devices have TTL input thresholds and a noise-filter at the input that prevents transient pulses from being passed to the output of the device.

A periodic update pulse is sent across the barrier to ensure the proper dc level of the output. If this dc-refresh pulse is not received, the input is assumed to be unpowered or not being actively driven, and the failsafe circuit drives the output to a logic high state. (See ISO7240CF (SLLS869) or contact TI for a logic low failsafe option).

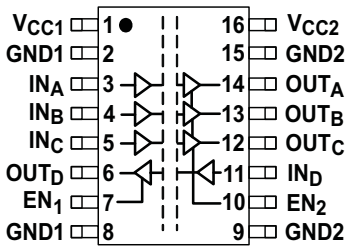
These devices may be powered from either 3.3-V or 5-V supplies on either side in any 3.3-V / 3.3-V, 5-V / 5-V, 5-V / 3.3-V, or 3.3-V / 5-V combination. Note that the signal input pins are 5-V tolerant regardless of the voltage supply level being used.

These devices are characterized for operation over the ambient temperature range of –40°C to 125°C.

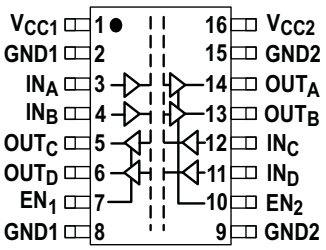
ISO7240A



ISO7241A



ISO7242A



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

FUNCTION DIAGRAM

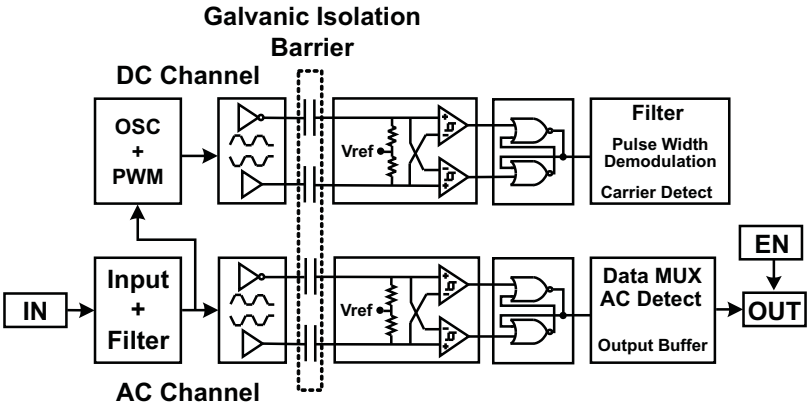


Table 1. Device Function Table ISO724x (1)

INPUT V_{CC}	OUTPUT V_{CC}	INPUT (IN)	OUTPUT ENABLE (EN)	OUTPUT (OUT)
PU	PU	H	H or Open	H
		L	H or Open	L
		X	L	Z
		Open	H or Open	H
PD	PU	X	H or Open	H
PD	PU	X	L	Z

(1) PU = Powered Up; PD = Powered Down ; X = Irrelevant; H = High Level; L = Low Level

AVAILABLE OPTIONS

PRODUCT	SIGNALING RATE	INPUT THRESHOLD	CHANNEL CONFIGURATION	MARKED AS	ORDERING NUMBER(1)
ISO7240ADW	1 Mbps	~1.5 V (TTL) (CMOS compatible)	4/0	ISO7240A	ISO7240ADW (rail)
					ISO7240ADWR (reel)
ISO7241ADW	1 Mbps	~1.5 V (TTL) (CMOS compatible)	3/1	ISO7241A	ISO7241ADW (rail)
					ISO7241ADWR (reel)
ISO7242ADW	1 Mbps	~1.5 V (TTL) (CMOS compatible)	2/2	ISO7242A	ISO7242ADW (rail)
					ISO7242ADWR (reel)

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

ABSOLUTE MAXIMUM RATINGS(1)

					VALUE	UNIT
V_{CC}	Supply voltage(2), V_{CC1}, V_{CC2}				–0.5 to 6	V
V_I	Voltage at IN, OUT, EN				–0.5 to 6	V
I_O	Output current				±15	mA
ESD	Electrostatic discharge	Human Body Model	JEDEC Standard 22, Test Method A114-C.01	All pins	±4	kV
		Field-Induced-Charged Device Model	JEDEC Standard 22, Test Method C101		±1	
		Machine Model	ANSI/ESDS5.2-1996		±200	V
T_J	Maximum junction temperature				170	°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values are with respect to network ground terminal and are peak voltage values.

RECOMMENDED OPERATING CONDITIONS

			MIN	TYP	MAX	UNIT
V_{CC}	Supply voltage(1), V_{CC1}, V_{CC2}		3.15		5.5	V
I_{OH}	High-level output current				4	mA
I_{OL}	Low-level output current		–4			mA
t_{ui}	Input pulse width	ISO724xA	1			µs
$1/t_{ui}$	Signaling rate	ISO724xA	0		1000	kbps
V_{IH}	High-level input voltage (IN) (EN on all devices)	ISO724xA	2		V_{CC}	V
V_{IL}	Low-level input voltage (IN) (EN on all devices)		0		0.8	V
T_J	Junction temperature				150	°C
H	External magnetic field-strength immunity per IEC 61000-4-8 and IEC 61000-4-9 certification				1000	A/m

(1) For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V.
For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.

IEC 60747-5-2 INSULATION CHARACTERISTICS(1)

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	SPECIFICATIONS	UNIT
V_{IORM}	Maximum working insulation voltage		560	V
V_{PR}	Input to output test voltage	After Input/Output Safety Test Subgroup 2/3 $V_{PR} = V_{IORM} \times 1.2$, t = 10 s, Partial discharge < 5 pC	672	V
		Method a, $V_{PR} = V_{IORM} \times 1.6$, Type and sample test with t = 10 s, Partial discharge < 5 pC	896	V
		Method b1, $V_{PR} = V_{IORM} \times 1.875$, 100 % Production test with t = 1 s, Partial discharge < 5 pC	1050	V
V_{IOTM}	Transient overvoltage	t = 60 s	4000	V
R_S	Insulation resistance	V_{IO} = 500 V at T_S	$>10^9$	Ω
	Pollution degree		2	

(1) Climatic Classification 40/125/21

ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} at 5-V[1] OPERATION

, over recommended operating conditions (unless otherwise noted)

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY CURRENT							
I_{CC1}	ISO7240A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_2 at 3 V		1	3	mA
		1 Mbps			1	3	
	ISO7241A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V		6.5	11	mA
		1 Mbps					
	ISO7242A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V		10	16	mA
		1 Mbps			10	16	
I_{CC2}	ISO7240A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_2 at 3 V		15	22	mA
		1 Mbps			16	22	
	ISO7241A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V		13	20	mA
		1 Mbps			13	20	
	ISO7242A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V		10	16	mA
		1 Mbps			10	16	
ELECTRICAL CHARACTERISTICS							
I_{OFF}	Sleep mode output current		EN at 0 V, Single channel		0		µA
V_{OH}	High-level output voltage		I_{OH} = –4 mA, See Figure 1	V_{CC} – 0.8			V
			I_{OH} = –20 µA, See Figure 1	V_{CC} – 0.1			
V_{OL}	Low-level output voltage		I_{OL} = 4 mA, See Figure 1			0.4	V
			I_{OL} = 20 µA, See Figure 1			0.1	
$V_{I(HYS)}$	Input voltage hysteresis				150		mV
I_{IH}	High-level input current		IN from 0 V to V_{CC}			10	µA
I_{IL}	Low-level input current			–10			
C_I	Input capacitance to ground		IN at V_{CC}, V_I = 0.4 sin (4E6πt)		2		pF
CMTI	Common-mode transient immunity		V_I = V_{CC} or 0 V, See Figure 4	25	50		kV/µs

(1) For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V.
For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.

SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} at 5-V OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay	See Figure 1	40		95	ns
PWD	Pulse-width distortion[1] $\lvert t_{PHL} - t_{PLH} \rvert$				10	
$t_{sk(o)}$	Channel-to-channel output skew [2]				2	ns
t_r	Output signal rise time	See Figure 1		2		ns
t_f	Output signal fall time			2		
t_{PHZ}	Propagation delay, high-level-to-high-impedance output	See Figure 2		15	20	ns
t_{PZH}	Propagation delay, high-impedance-to-high-level output			15	20	
t_{PLZ}	Propagation delay, low-level-to-high-impedance output			15	20	
t_{PZL}	Propagation delay, high-impedance-to-low-level output			15	20	
t_{fs}	Failsafe output delay time from input power loss	See Figure 3		12		µs

(1) Also referred to as pulse skew.
(2) $t_{sk(o)}$ is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.

ELECTRICAL CHARACTERISTICS: V_{CC1} at 5-V, V_{CC2} at 3.3-V(1) OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER			TEST CONDITIONS		MIN	TYP	MAX	UNIT
SUPPLY CURRENT								
I_{CC1}	ISO7240A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_2 at 3 V			1	3	mA
		1 Mbps				1	3	
	ISO7241A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V			6.5	11	mA
		1 Mbps						
	ISO7242A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V			10	16	mA
		1 Mbps				10	16	
I_{CC2}	ISO7240A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_2 at 3 V			9.5	15	mA
		1 Mbps				10	15	
	ISO7241A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V			8	13	mA
		1 Mbps				8	13	
	ISO7242A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V			6	10	mA
		1 Mbps				6	10	
ELECTRICAL CHARACTERISTICS								
I_{OFF}	Sleep mode output current		EN at 0 V, Single channel			0		µA
V_{OH}	High-level output voltage		I_{OH} = –4 mA, See Figure 1	ISO7240A	V_{CC} – 0.4			V
				ISO724x (5-V side)	V_{CC} – 0.8			
			I_{OH} = –20 µA, See Figure 1		V_{CC} – 0.1			
V_{OL}	Low-level output voltage		I_{OL} = 4 mA, See Figure 1				0.4	V
			I_{OL} = 20 µA, See Figure 1				0.1	
$V_{I(HYS)}$	Input voltage hysteresis					150		mV
I_{IH}	High-level input current		IN from 0 V to V_{CC}				10	µA
I_{IL}	Low-level input current				–10			
C_I	Input capacitance to ground		IN at V_{CC}, V_I = 0.4 sin (4E6πt)			2		pF
CMTI	Common-mode transient immunity		V_I = V_{CC} or 0 V, See Figure 4		25	50		kV/µs

(1) For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V.
For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.

SWITCHING CHARACTERISTICS: V_{CC1} at 5-V, V_{CC2} at 3.3-V OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay	See Figure 1	40		100	ns
PWD	Pulse-width distortion(1) $\lvert t_{PHL} - t_{PLH} \rvert$				11	
$t_{sk(o)}$	Channel-to-channel output skew (2)				3	ns
				0	1	
t_r	Output signal rise time	See Figure 1		2		ns
t_f	Output signal fall time			2		
t_{PHZ}	Propagation delay, high-level-to-high-impedance output	See Figure 2		15	20	ns
t_{PZH}	Propagation delay, high-impedance-to-high-level output			15	20	
t_{PLZ}	Propagation delay, low-level-to-high-impedance output			15	20	
t_{PZL}	Propagation delay, high-impedance-to-low-level output			15	20	
t_{fs}	Failsafe output delay time from input power loss	See Figure 3		18		µs

(1) Also known as pulse skew
(2) $t_{sk(o)}$ is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.

ELECTRICAL CHARACTERISTICS: V_{CC1} at 3.3-V, V_{CC2} at 5-V(1) OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER			TEST CONDITIONS		MIN	TYP	MAX	UNIT
SUPPLY CURRENT								
I_{CC1}	ISO7240A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_2 at 3 V			0.5	1	mA
		1 Mbps				1	2	
	ISO7241A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V			4	7	mA
		1 Mbps				4	7	
	ISO7242A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V			6	10	mA
		1 Mbps				6	10	
I_{CC2}	ISO7240A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_2 at 3 V			15	22	mA
		1 Mbps				16	22	
	ISO7241A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V			13	20	mA
		1 Mbps				13	20	
	ISO7242A	Quiescent	V_I = V_{CC} or 0 V, All channels, no load, EN_1 at 3 V, EN_2 at 3 V			10	16	mA
		1 Mbps				10	16	
ELECTRICAL CHARACTERISTICS								
I_{OFF}	Sleep mode output current		EN at V_{CC}, Single channel			0		µA
V_{OH}	High-level output voltage		I_{OH} = –4 mA, See Figure 1	ISO7240A	V_{CC} – 0.4			V
				ISO724x (5-V side)	V_{CC} – 0.8			
			I_{OH} = –20 µA, See Figure 1		V_{CC} – 0.1			
V_{OL}	Low-level output voltage		I_{OL} = 4 mA, See Figure 1				0.4	V
			I_{OL} = 20 µA, See Figure 1				0.1	
$V_{I(HYS)}$	Input voltage hysteresis					150		mV
I_{IH}	High-level input current		IN from 0 V to V_{CC}				10	µA
I_{IL}	Low-level input current				–10			
C_I	Input capacitance to ground		IN at V_{CC}, V_I = 0.4 sin (4E6πt)			2		pF
CMTI	Common-mode transient immunity		V_I = V_{CC} or 0 V, See Figure 4		25	50		kV/µs

(1) For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V.
For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.

SWITCHING CHARACTERISTICS: V_{CC1} at 3.3-V and V_{CC2} at 5-V OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay	See Figure 1	40		100	ns
PWD	Pulse-width distortion(1) $\lvert t_{PHL} - t_{PLH} \rvert$				11	
$t_{sk(o)}$	Channel-to-channel output skew (2)				2.5	ns
				0	1	
t_r	Output signal rise time	See Figure 1		2		ns
t_f	Output signal fall time			2		
t_{PHZ}	Propagation delay, high-level-to-high-impedance output	See Figure 2		15	20	ns
t_{PZH}	Propagation delay, high-impedance-to-high-level output			15	20	
t_{PLZ}	Propagation delay, low-level-to-high-impedance output			15	20	
t_{PZL}	Propagation delay, high-impedance-to-low-level output			15	20	
t_{fs}	Failsafe output delay time from input power loss	See Figure 3		12		µs

(1) Also known as pulse skew
(2) $t_{sk(o)}$ is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.

ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3 V(1) OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY CURRENT							
I_{CC1}	ISO7240A	Quiescent	V_I = V_{CC} or 0 V, all channels, no load, EN_2 at 3 V		0.5	1	mA
		1 Mbps			1	2	
	ISO7241A	Quiescent	V_I = V_{CC} or 0 V, all channels, no load, EN_1 at 3 V, EN_2 at 3 V		4	7	mA
		1 Mbps			4	7	
	ISO7242A	Quiescent	V_I = V_{CC} or 0 V, all channels, no load, EN_1 at 3 V, EN_2 at 3 V		6	10	
		1 Mbps			6	10	
I_{CC2}	ISO7240A	Quiescent	V_I = V_{CC} or 0 V, all channels, no load, EN_2 at 3 V		9.5	15	mA
		1 Mbps			10	15	
	ISO7241A	Quiescent	V_I = V_{CC} or 0 V, all channels, no load, EN_1 at 3 V, EN_2 at 3 V		8	13	mA
		1 Mbps			8	13	
	ISO7242A	Quiescent	V_I = V_{CC} or 0 V, all channels, no load, EN_1 at 3 V, EN_2 at 3 V		6	10	
		1 Mbps			6	10	
ELECTRICAL CHARACTERISTICS							
I_{OFF}	Sleep mode output current		EN at 0 V, single channel		0		µA
V_{OH}	High-level output voltage		I_{OH} = –4 mA, See Figure 1	V_{CC} – 0.4			V
			I_{OH} = –20 µA, See Figure 1	V_{CC} – 0.1			
V_{OL}	Low-level output voltage		I_{OL} = 4 mA, See Figure 1			0.4	V
			I_{OL} = 20 µA, See Figure 1			0.1	
$V_{I(HYS)}$	Input voltage hysteresis				150		mV
I_{IH}	High-level input current		IN from 0 V or V_{CC}			10	µA
I_{IL}	Low-level input current			–10			
C_I	Input capacitance to ground		IN at V_{CC}, V_I = 0.4 sin (4E6πt)		2		pF
CMTI	Common-mode transient immunity		V_I = V_{CC} or 0 V, See Figure 4	25	50		kV/µs

(1) For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V.
For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.

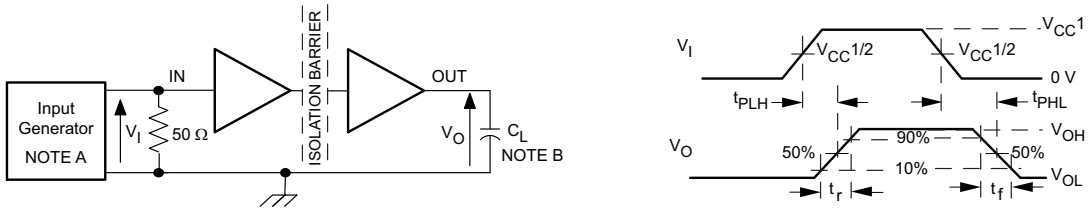
SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3-V OPERATION

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay	See Figure 1	45		110	ns
PWD	Pulse-width distortion $\lvert t_{PHL} - t_{PLH} \rvert$ (1)				12	
$t_{sk(o)}$	Channel-to-channel output skew (2)				3.5	ns
				0	1	
t_r	Output signal rise time	See Figure 1		2		
t_f	Output signal fall time			2		
t_{PHZ}	Propagation delay, high-level-to-high-impedance output	See Figure 2		15	20	ns
t_{PZH}	Propagation delay, high-impedance-to-high-level output			15	20	
t_{PLZ}	Propagation delay, low-level-to-high-impedance output			15	20	
t_{PZL}	Propagation delay, high-impedance-to-low-level output			15	20	
t_{fs}	Failsafe output delay time from input power loss	See Figure 3		18		µs

(1) Also referred to as pulse skew.
(2) $t_{sk(o)}$ is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.

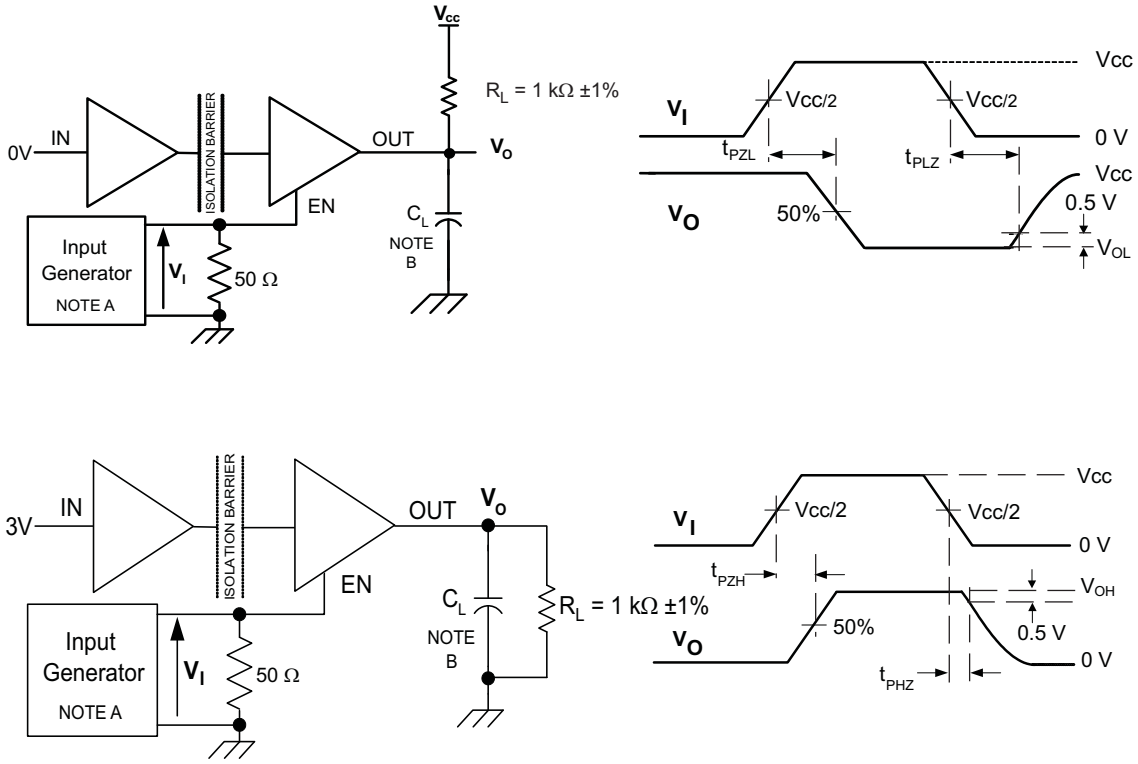
PARAMETER MEASUREMENT INFORMATION



A. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 50 kHz, 50% duty cycle, t_r ≤ 3 ns, t_f ≤ 3 ns, Z_O = 50Ω.

B. C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

Figure 1. Switching Characteristic Test Circuit and Voltage Waveforms

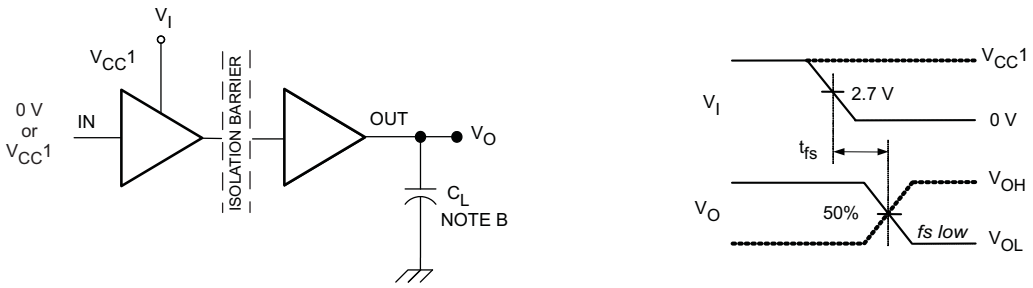


A. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 50 kHz, 50% duty cycle, t_r ≤ 3 ns, t_f ≤ 3 ns, Z_O = 50Ω.

B. C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

Figure 2. Enable/Disable Propagation Delay Time Test Circuit and Waveform

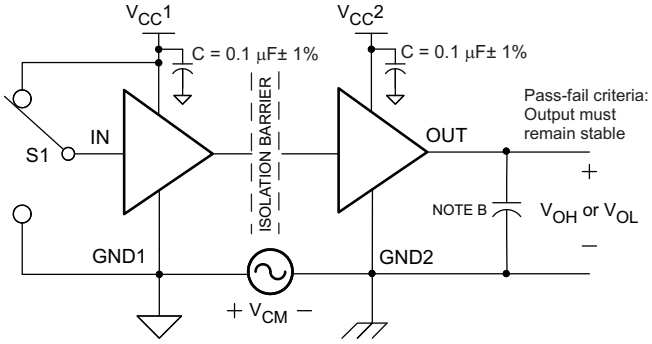
PARAMETER MEASUREMENT INFORMATION (continued)



A. C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

B. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 50 kHz, 50% duty cycle, t_r ≤ 3 ns, t_f ≤ 3 ns, Z_O = 50Ω.

Figure 3. Failsafe Delay Time Test Circuit and Voltage Waveforms



A. C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

B. The input pulse is supplied by a generator having the following characteristics: PRR ≤ 50 kHz, 50% duty cycle, t_r ≤ 3 ns, t_f ≤ 3 ns, Z_O = 50Ω.

Figure 4. Common-Mode Transient Immunity Test Circuit and Voltage Waveform

DEVICE INFORMATION

PACKAGE CHARACTERISTICS

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01)	Minimum air gap (Clearance)	Shortest terminal-to-terminal distance through air	8.34			mm
L(I02)	Minimum external tracking (Creepage)	Shortest terminal-to-terminal distance across the package surface	8.1			mm
C_{TI}	Tracking resistance (comparative tracking index)	DIN IEC 60112/VDE 0303 Part 1	≥ 175			V
	Minimum Internal Gap (Internal Clearance)	Distance through the insulation	0.008			mm
R_{IO}	Isolation resistance	Input to output, V_{IO} = 500 V, all pins on each side of the barrier tied together creating a two-terminal device		$>10^{12}$		Ω
C_{IO}	Barrier capacitance Input to output	V_I = 0.4 sin (4E6πt)		2		pF
C_I	Input capacitance to ground	V_I = 0.4 sin (4E6πt)		2		pF

IEC 60664-1 RATINGS TABLE

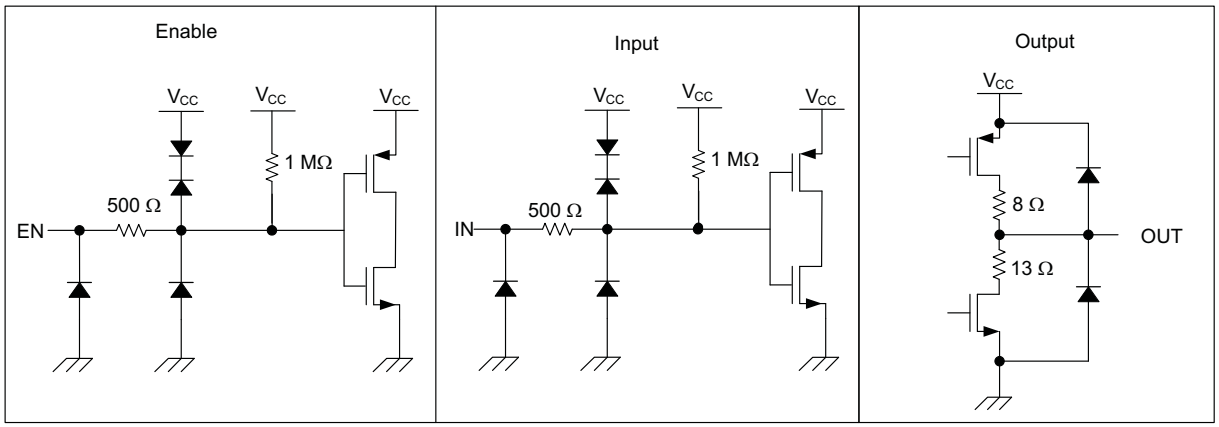
PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic isolation group	Material group	IIIa
Installation classification	Rated mains voltage ≤150 VRMS	I-IV
	Rated mains voltage ≤300 VRMS	I-III

REGULATORY INFORMATION

VDE	CSA	UL
Certified according to IEC 60747-5-2	Approved under CSA Component Acceptance Notice	Recognized under 1577 Component Recognition Program(1)
File Number: 40016131	File Number: 1698195	File Number: E181974

(1) Production tested ≥ 3000 Vrms for 1 second in accordance with UL 1577.

DEVICE I/O SCHEMATICS



THERMAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
θ_{JA}	Junction-to-air	Low-K Thermal Resistance(1)		168		°C/W
		High-K Thermal Resistance		96.1		
θ_{JB}	Junction-to-Board Thermal Resistance			61		°C/W
θ_{JC}	Junction-to-Case Thermal Resistance			48		°C/W
P_D	Device Power Dissipation	$V_{CC1} = V_{CC2} = 5.5$ V, $T_J = 150°C$, $C_L = 15$ pF, Input a 50% duty cycle square wave			220	mW

(1) Tested in accordance with the Low-K or High-K thermal metric definitions of EIA/JESD51-3 for leaded surface mount packages.

TYPICAL CHARACTERISTIC CURVES

INPUT VOLTAGE THRESHOLD vs FREE-AIR TEMPERATURE

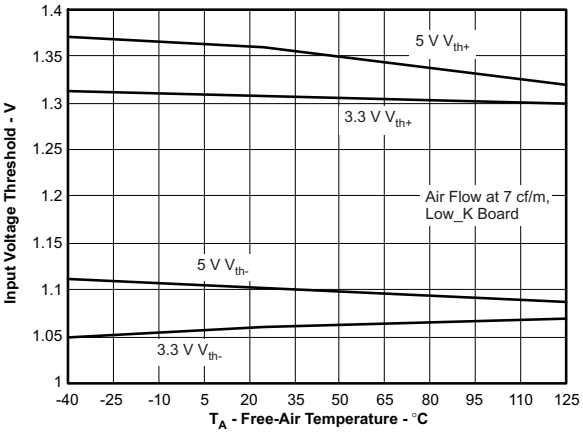


Figure 5.

V_{CC1} FAILSAFE THRESHOLD vs FREE-AIR TEMPERATURE

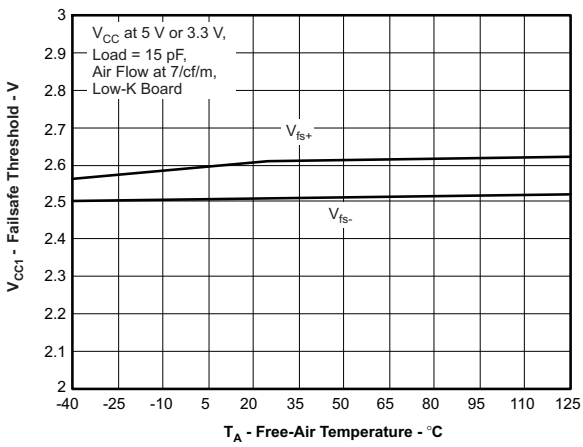


Figure 6.

HIGH-LEVEL OUTPUT CURRENT vs HIGH-LEVEL OUTPUT VOLTAGE

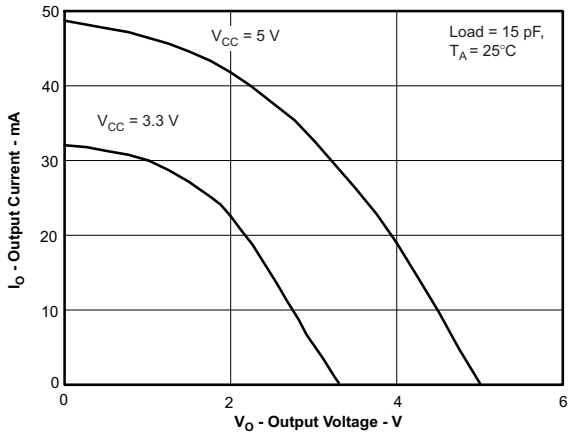


Figure 7.

LOW-LEVEL OUTPUT CURRENT vs LOW-LEVEL OUTPUT VOLTAGE

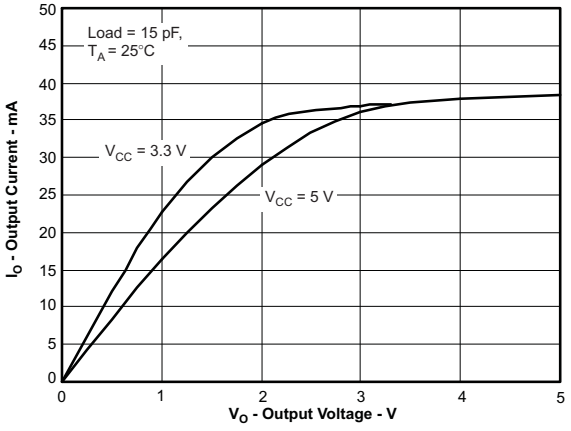


Figure 8.

APPLICATION INFORMATION

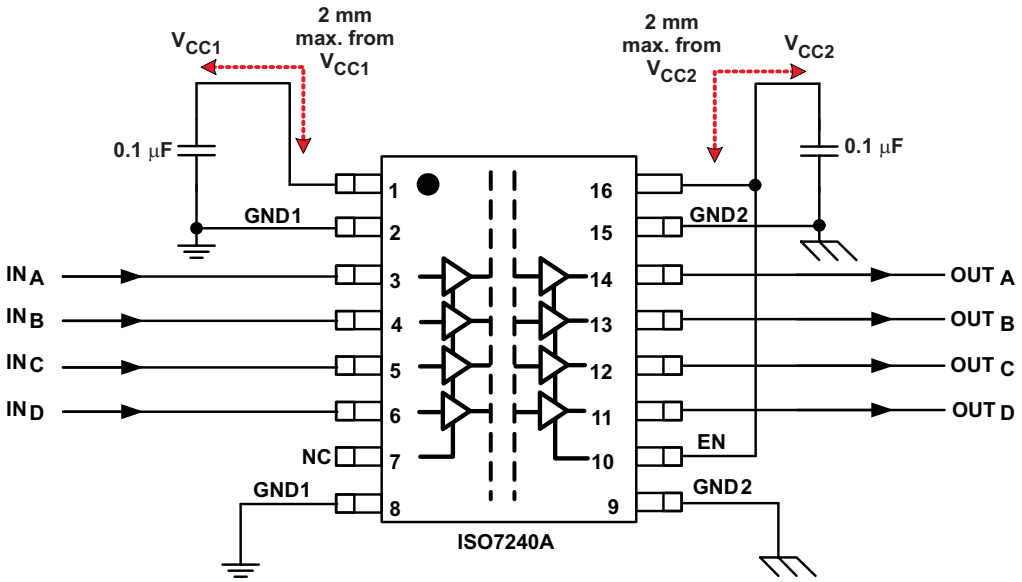


Figure 9. Typical ISO7240A Application Circuit

LIFE EXPECTANCY vs. WORKING VOLTAGE

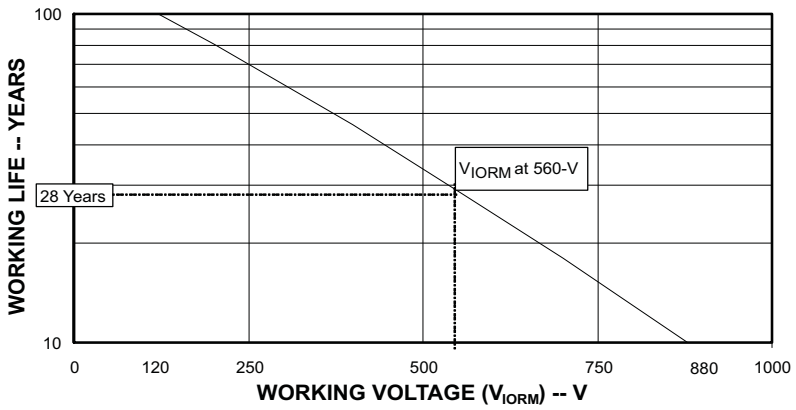


Figure 10. Time-Dependant Dielectric Breakdown Testing Results

PRODUCT NOTIFICATION

An ISO724xA anomaly occurs when a negative-going pulse below the specified 1 μs minimum bit width is input to the device. The output locks in a logic-low condition until the next rising edge occurs after a 1 μs period.

Positive noise edges in pulses of less than the minimum specified 1 μs have no effect on the device, and are properly filtered.

To prevent noise from interfering with ISO724xA performance, it is recommended that an appropriately sized capacitor be placed on each input of the device

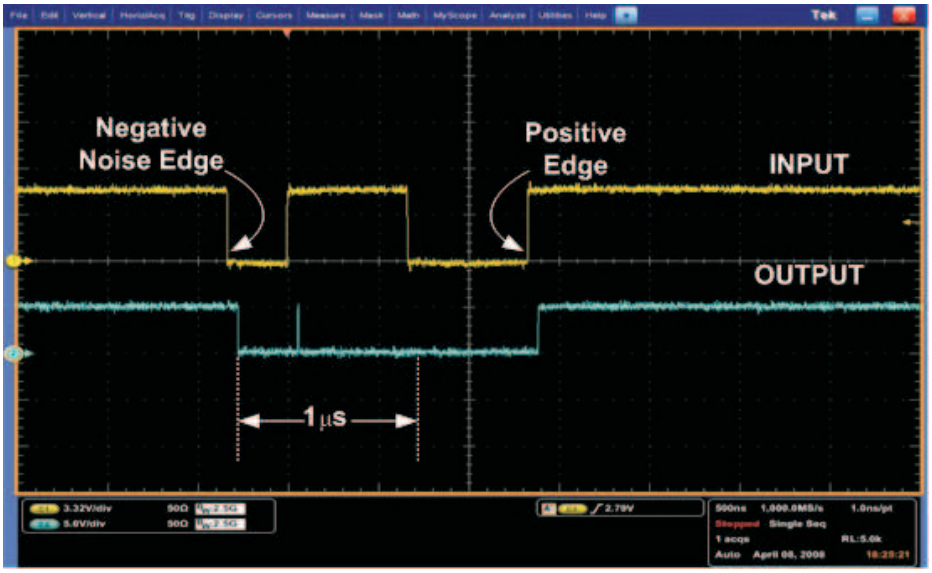


Figure 11. ISO724xA Anomaly

REVISION HISTORY

Changes from Original (May 2008) to Revision A	Page
• Changed In the PACKAGE CHARACTERISTICS table, line 1, change $L_{(IO1)}$ MIN value from 7.7mm to 8.34mm.	10

Changes from Revision A (July 2008) to Revision B	Page
• Added information to the 1st Feature bullet to include CSA and IEC 60950-1 certification	1
• Changed Figure 9 From: 20mm max.from V_{CCx} To: 2mm max. from V_{CCx}.	12

Changes from Revision B (December 2008) to Revision C	Page
• Changed I_{CC1} for Quiescent and 1Mbps From: 10mA To: 11mA	4
• Changed I_{CC1} for Quiescent and 1Mbps From: 10mA To: 11mA	5

Changes from Revision C (March 2009) to Revision D	Page
• Changed The Input circuit in the DEVICE I/O SCHEMATICS illustration.	10

Changes from Revision D (December 2009) to Revision E **Page**

- Added the IEC 60747-5-2 INSULATION CHARACTERISTIC table 3
- Added C_{TI} - Tracking resistance (comparative tracking index to the PACKAGE CHARACTERISTICS table 10
- Added the IEC 60664-1 RATINGS TABLE 10

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ISO7240ADW	NRND	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7240A	
ISO7240ADWG4	NRND	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7240A	
ISO7240ADWR	NRND	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7240A	
ISO7240ADWRG4	NRND	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7240A	
ISO7241ADW	NRND	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7241A	
ISO7241ADWG4	NRND	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7241A	
ISO7241ADWR	NRND	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7241A	
ISO7241ADWRG4	NRND	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7241A	
ISO7242ADW	NRND	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7242A	
ISO7242ADWG4	NRND	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7242A	
ISO7242ADWR	NRND	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7242A	
ISO7242ADWRG4	NRND	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7242A	

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF ISO7241A :

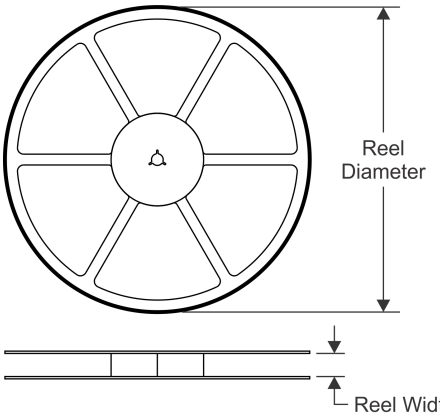
- Enhanced Product: ISO7241A-EP

NOTE: Qualified Version Definitions:

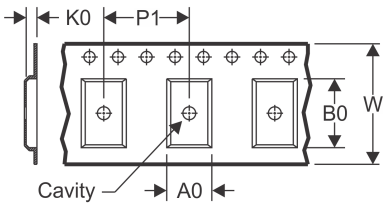
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION

REEL DIMENSIONS

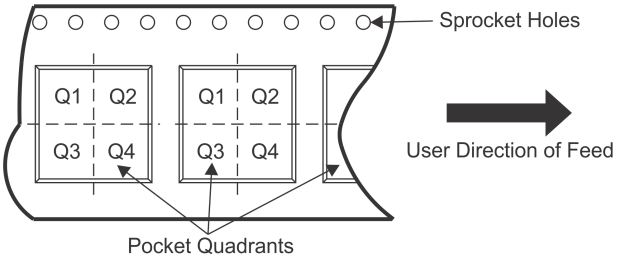


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

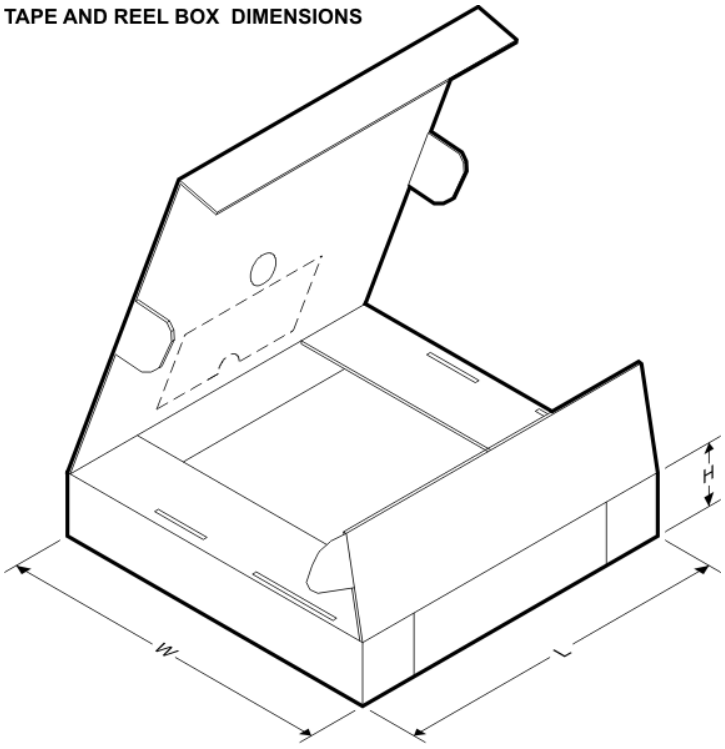


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7240ADWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7241ADWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7242ADWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

PACKAGE MATERIALS INFORMATION

TAPE AND REEL BOX DIMENSIONS

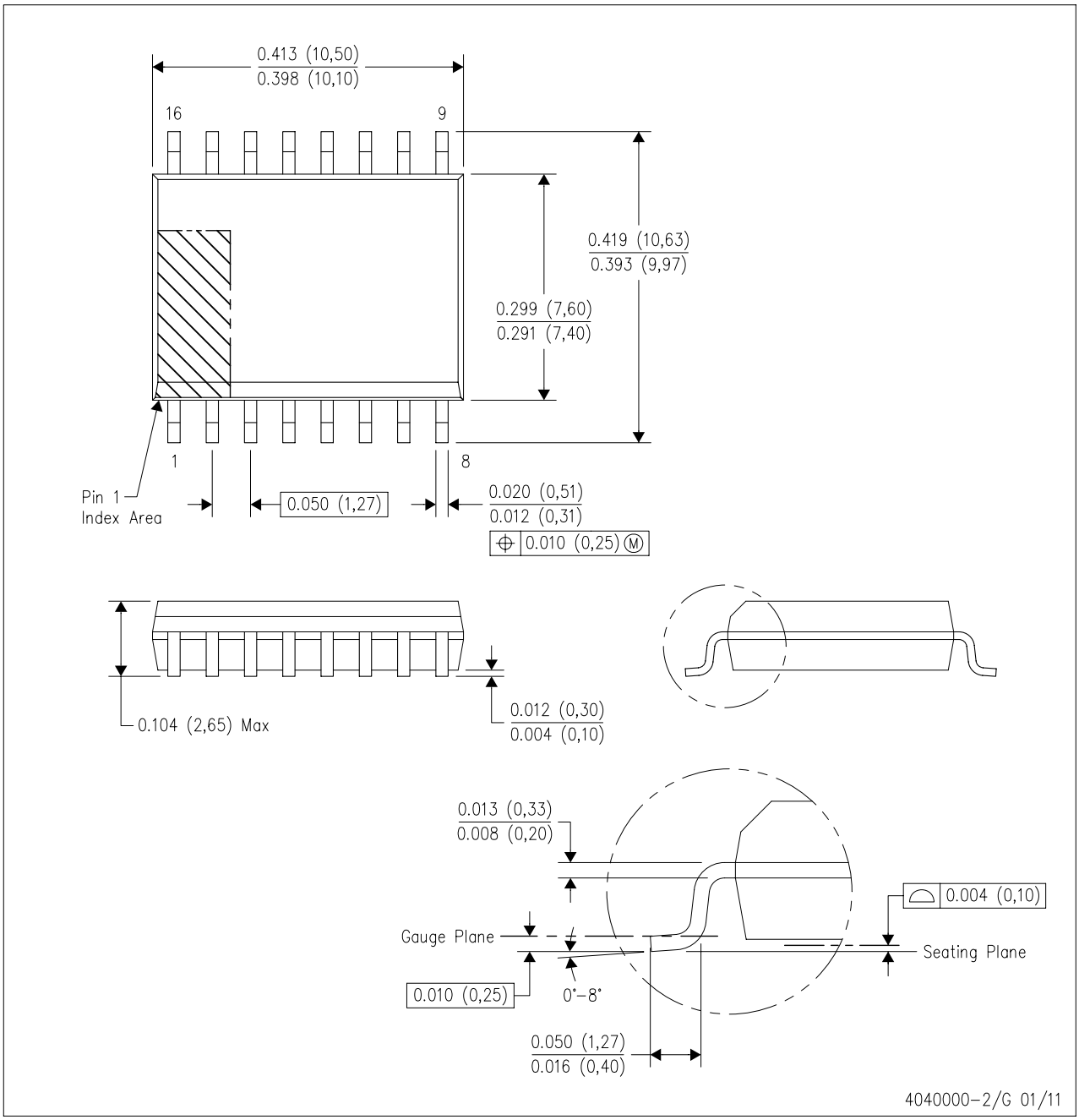


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7240ADWR	SOIC	DW	16	2000	367.0	367.0	38.0
ISO7241ADWR	SOIC	DW	16	2000	367.0	367.0	38.0
ISO7242ADWR	SOIC	DW	16	2000	367.0	367.0	38.0

MECHANICAL DATA

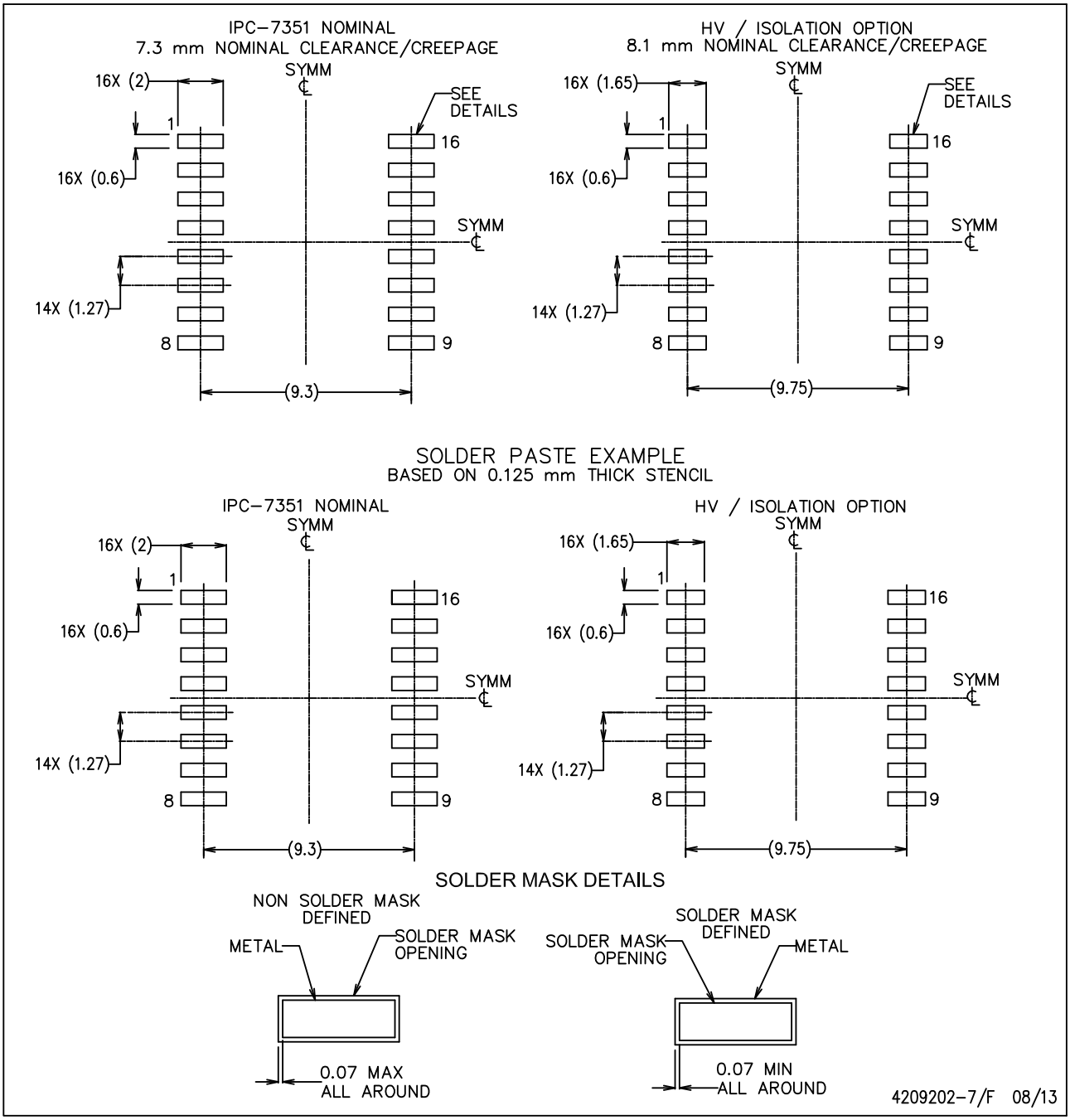
DW (R–PDSO–G16) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–013 variation AA.

LAND PATTERN DATA

DW (R-PDSO-G16) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Refer to IPC7351 for alternate board design.
D. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
E. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
F. Board assembly site may have different recommendations for stencil design.

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as “components”) are sold subject to TI’s terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI’s terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers’ products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers’ products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI’s goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or “enhanced plastic” are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have ***not*** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		**Applications**	
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com		
OMAP Applications Processors	www.ti.com/omap	**TI E2E Community**	e2e.ti.com
Wireless Connectivity	www.ti.com/wirelessconnectivity		

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265